60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
60V	23mΩ @ V_{GS} = 10V	50A
	28mΩ @ V_{GS} = 4.5V	45A

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMNH6021SK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

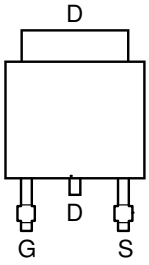
- Power management
- Driving solenoids
- Motor control

Mechanical Data

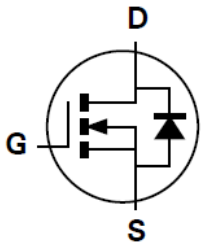
- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.33 grams (Approximate)

TO252 (DPAK)

Top View



Pinout Top View



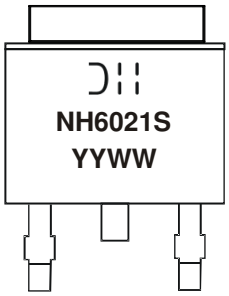
Equivalent Circuit

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMNH6021SK3Q-13	TO252 (DPAK)	2,500	Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
NH6021S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 25 = 2025)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	T_C = +25°C T_C = +100°C	I_D	50 35	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	80	A
Maximum Body Diode Forward Current (Note 7)		I_S	40	A
Avalanche Current, L = 0.1mH (Note 8)		I_{AS}	35	A
Avalanche Energy, L = 0.1mH (Note 8)		E_{AS}	64	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	73	°C/W
Total Power Dissipation (Note 6)		P_D	3.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.8	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	13	23	mΩ	V_{GS} = 10V, I_D = 12A
		—	18	28		V_{GS} = 4.5V, I_D = 12A
Diode Forward Voltage	V_{SD}	—	0.75	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	1143	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	168	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	69	—	pF	
Gate Resistance	R_g	—	2.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	20.1	—	nC	V_{DS} = 30V, I_D = 20A
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	12.1	—	nC	
Gate-Source Charge	Q_{gs}	—	4.3	—	nC	
Gate-Drain Charge	Q_{gd}	—	5.5	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.4	—	ns	V_{DD} = 30V, V_{GS} = 10V, R_G = 4.7Ω, I_D = 10A
Turn-On Rise Time	t_R	—	6.0	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	14.2	—	ns	
Turn-Off Fall Time	t_F	—	5.4	—	ns	
Reverse-Recovery Time	t_{RR}	—	21.2	—	ns	I_F = 20A, di/dt = 100A/µs
Reverse-Recovery Charge	Q_{RR}	—	15.2	—	nC	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

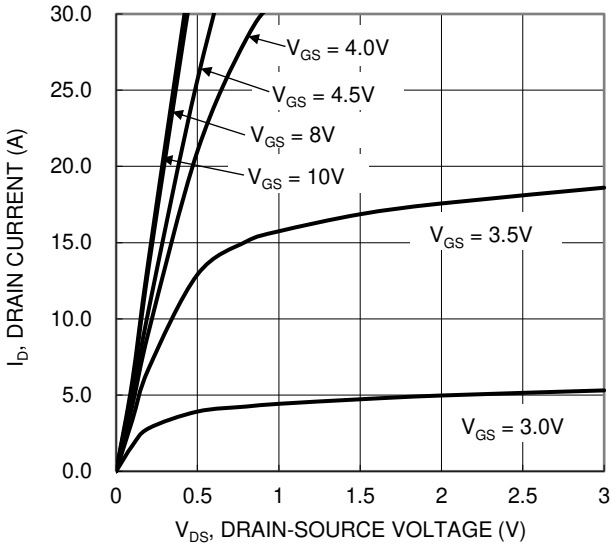


Figure 1. Typical Output Characteristic

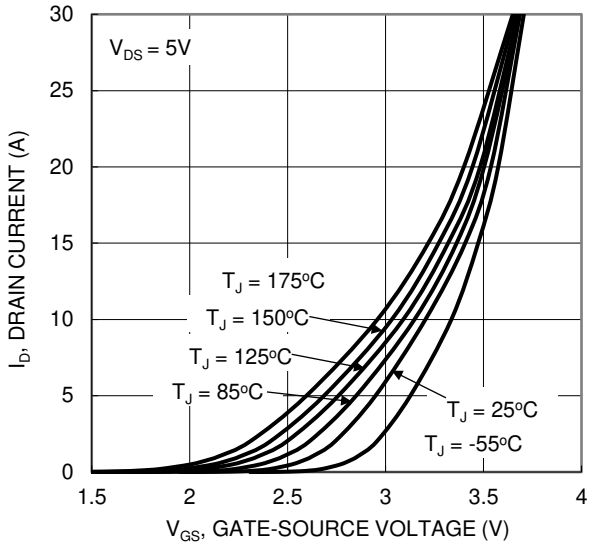


Figure 2. Typical Transfer Characteristic

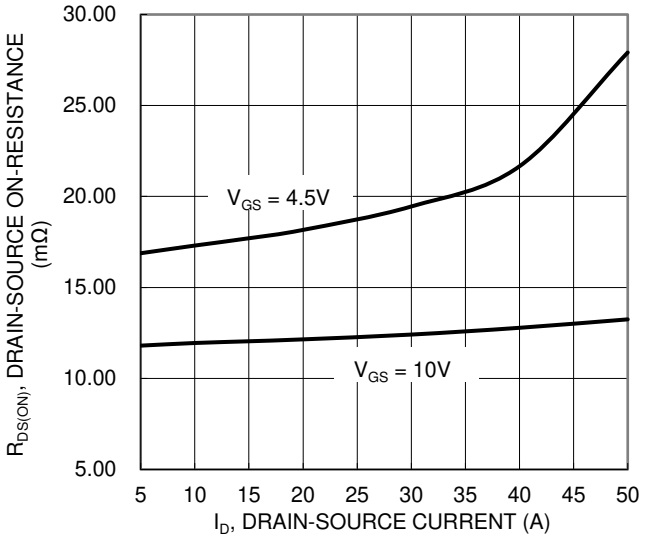


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

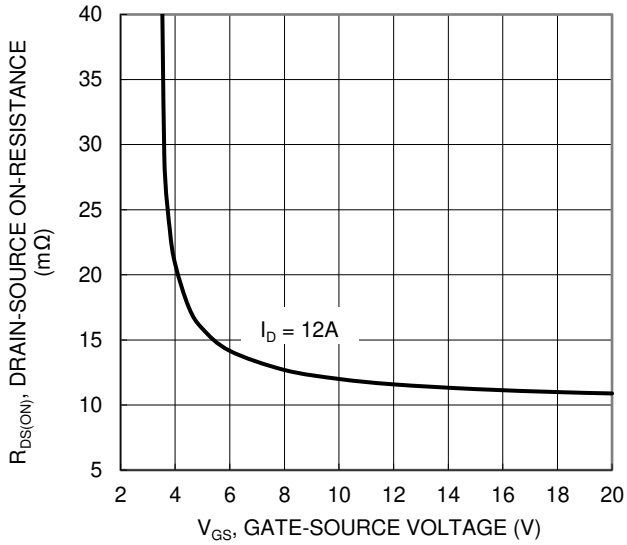


Figure 4. Typical Transfer Characteristic

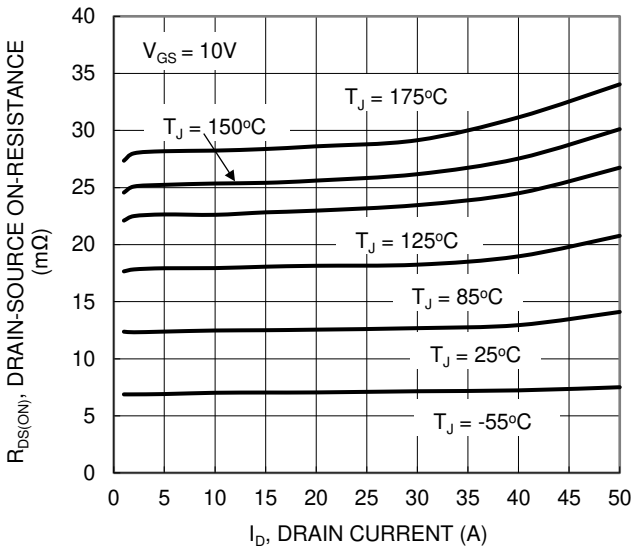


Figure 5. Typical On-Resistance vs Drain Current and Temperature

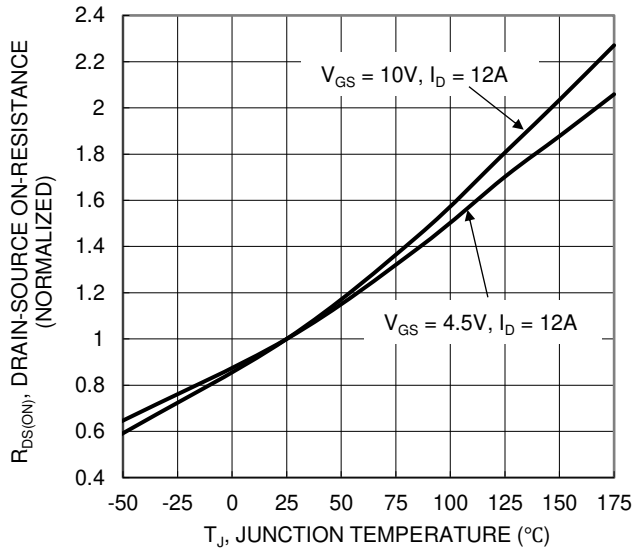


Figure 6. On-Resistance Variation with Temperature

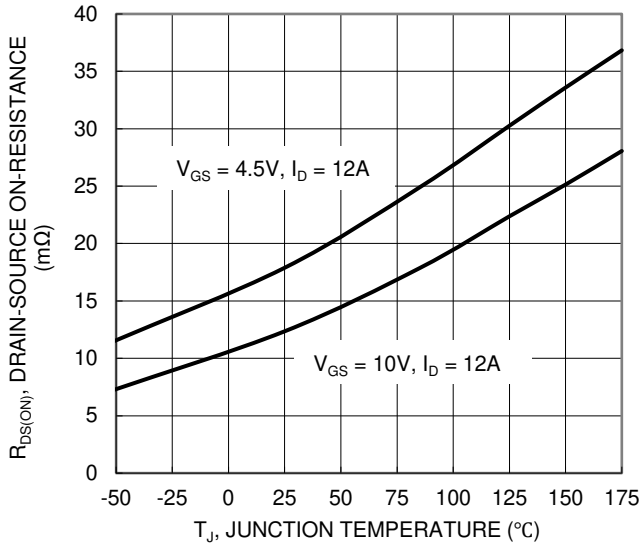


Figure 7. On-Resistance Variation with Temperature

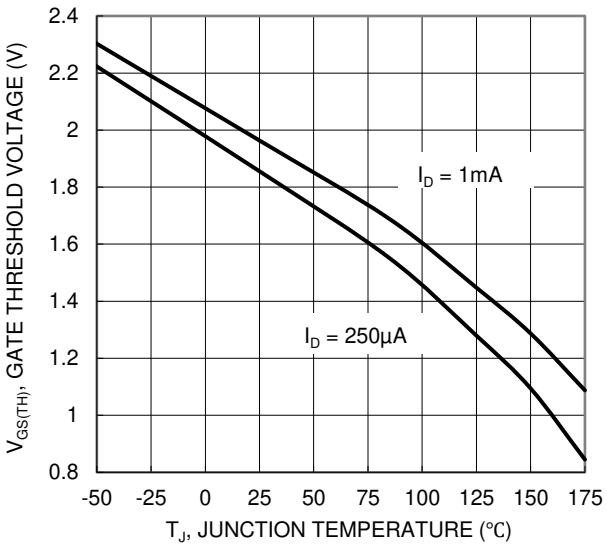


Figure 8. Gate Threshold Variation vs Junction Temperature

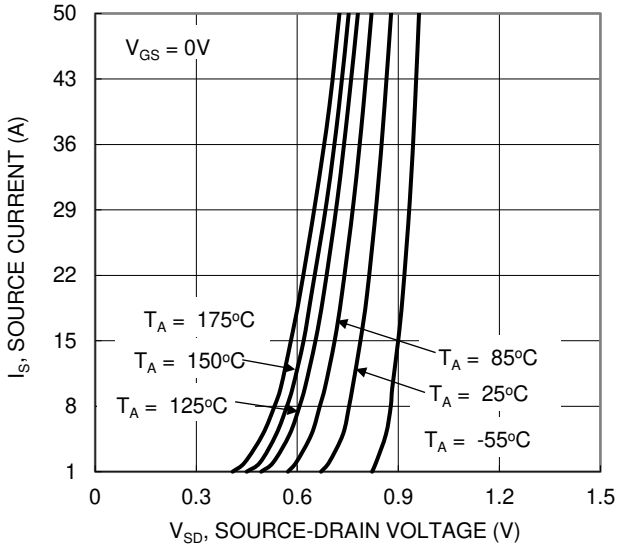


Figure 9. Diode Forward Voltage vs. Current

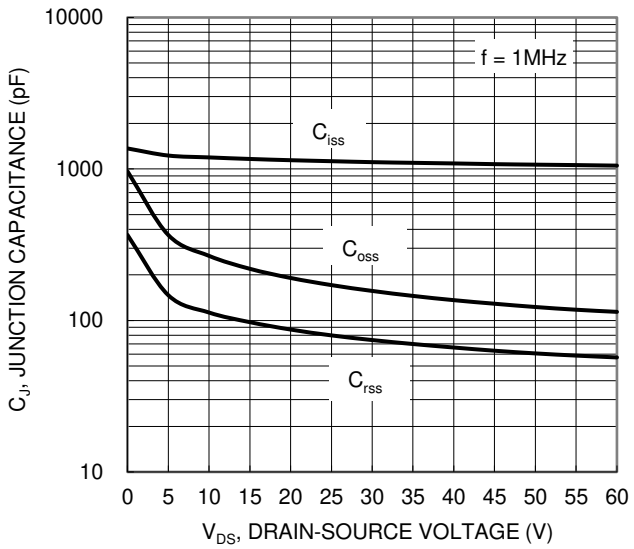


Figure 10. Typical Junction Capacitance

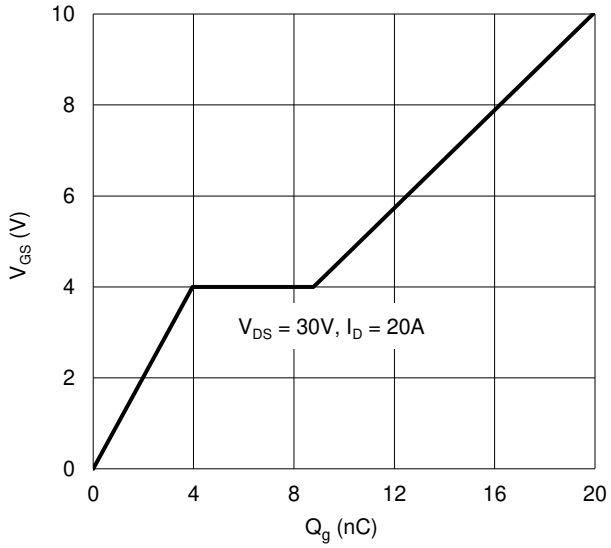


Figure 11. Gate Charge

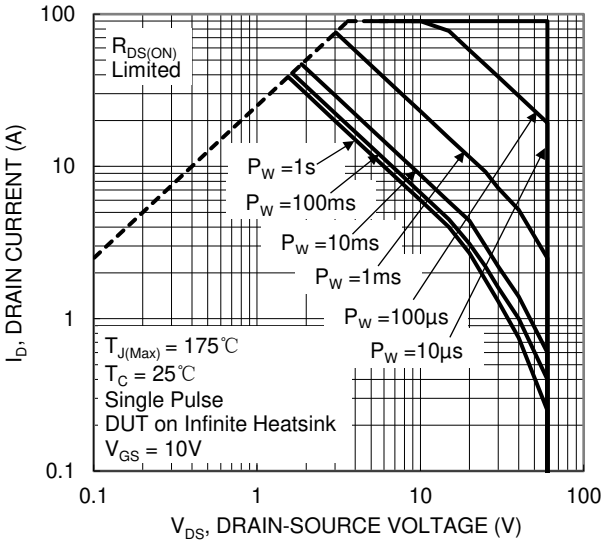


Figure 12. SOA, Safe Operation Area

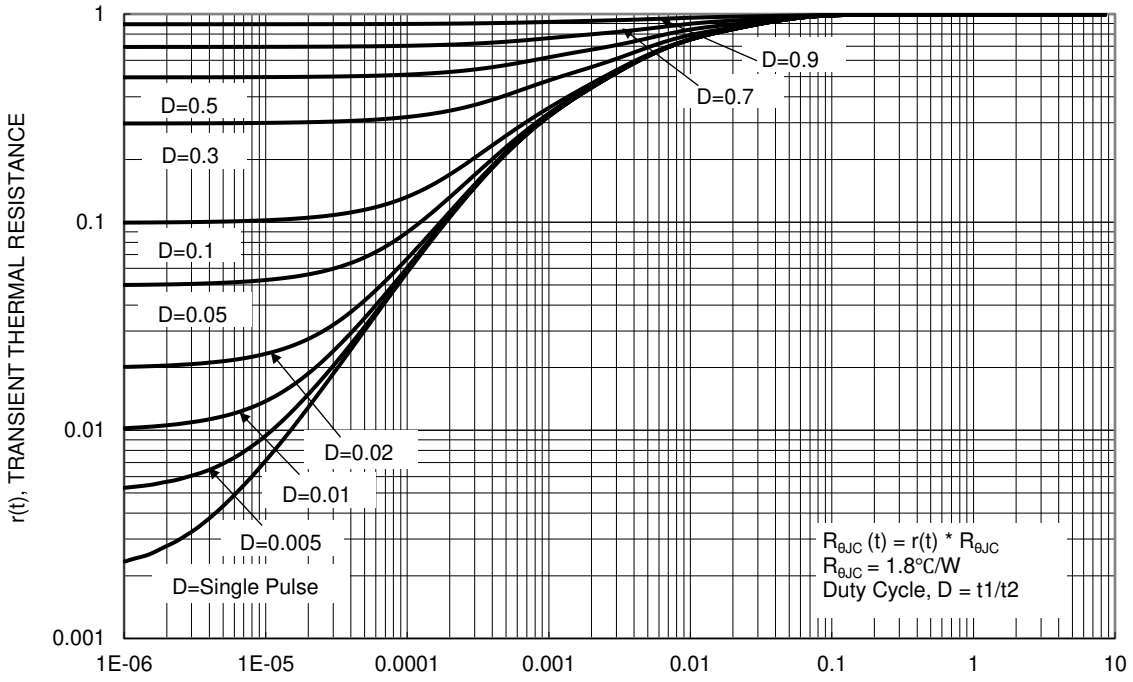
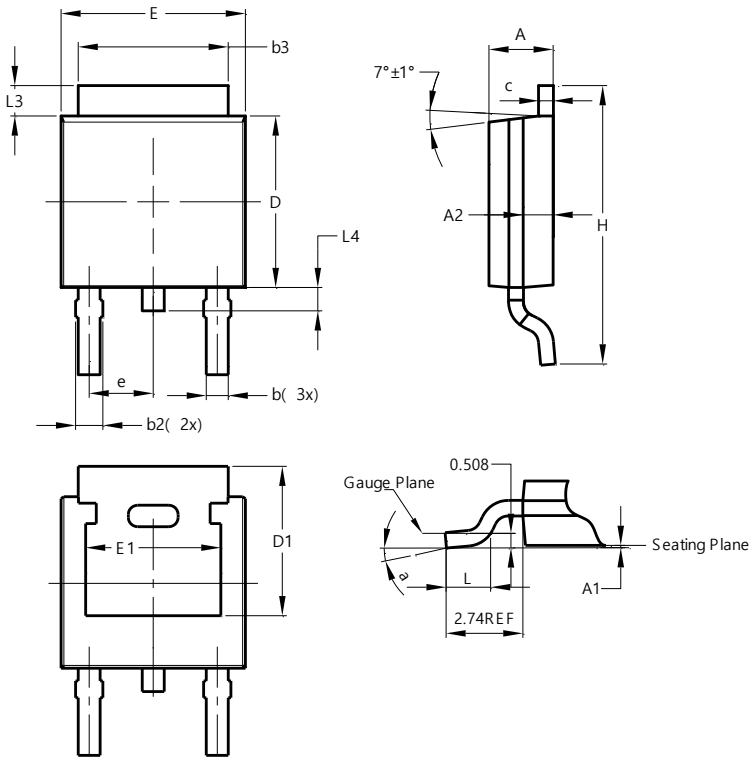


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

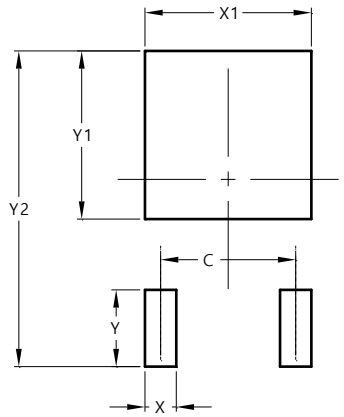


TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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